

# Quad 2-Input NOR Gate High-Performance Silicon-Gate CMOS

### **FEATURES**

Output Drive Capability: 10 LSTTL Loads

Outputs Directly Interface to CMOS, NMOS, and TTL

Operating Voltage Range: 2.0 to 6.0 V

Low Input Current: 1.0 A

High Noise Immunity Characteristic of CMOS Devices

 In Compliance with the Requirements Defined by JEDEC Standard No. 7A

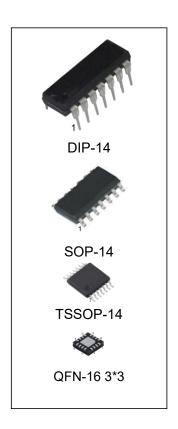
• ESD Performance:

HBM 2000 V;

Machine Model 200 V

• Chip Complexity: 40 FETs or 10 Equivalent Gates

These are Pb-Free Devices

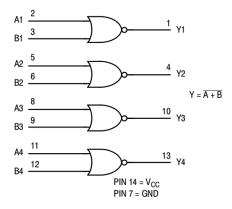


#### ORDERING INFORMATION

DEVICE	Package Type	MARKING	Packing	Packing Qty
74HC02N	DIP-14	74HC02	TUBE	1000pcs/box
74HC02M/TR	SOP-14	74HC02	REEL	2500pcs/reel
74HC02MT/TR	TSSOP-14	HC02	REEL	2500pcs/reel
74HC02LQ/TR	QFN-16 3*3	HC02	REEL	5000pcs/reel



# **LOGIC DIAGRAM**

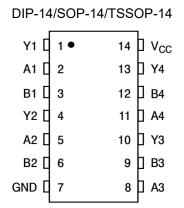


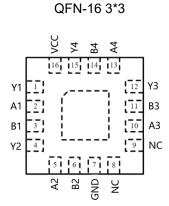
## **FUNCTION TABLE**

Inp	Output	
Α	Y	
L	L	Н
L	н	L
Н	L	L
н	н	L



#### **PIN ASSIGNMENT**





#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
Vin	DC Input Voltage (Referenced to GND)	- 0.5 to VCC + 0.5	V
Vout	DC Output Voltage (Referenced to GND)	- 0.5 to VCC + 0.5	V
lin	DC Input Current, per Pin	20	mA
lout	DC Output Current, per Pin	25	mA
ICC	DC Supply Current, VCC and GND Pins	50	mA
PD	Power Dissipation in Still Air, SOP Package TSSOP Package	500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds SOP or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance cir- cuit. For proper operation, Vin and Vout should be constrained to the range  $GND \le (Vin \text{ or Vout}) \le VCC$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND = VCC). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Derating SOP Package: 7 mW/°C from 65° to 125°C ; TSSOP Package: 6.1 mW/°C from 65° to 125°C

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Paramet	Min	Max	Unit	
Vcc	DC Supply Voltage (Referenced to GNI	2.0	6.0	V	
Vin, Vout	DC Input Voltage, Output Voltage (Refe	0	Vcc	V	
TA	Operating Temperature, All Package Ty	-40	+ 85	°C	
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time(Figure 1)	VCC = 2.0 V VCC = 4.5 V VCC = 6.0 V	0 0 0	1000 500 400	ns



# DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			Vcc	Gua	ranteed L	imit	
Symbol	Parameter	Test Conditions	(V)	-40 to 25°C	≤85°C	≤125°C	Unit
			2.0	1.5	1.5	1.5	
VIH	Minimum High-Level Input	Vout = 0.1 V or VCC - 0.1 V	3.0	2.1	2.1	2.1	v l
* 1111	Voltage	lout  ≤ 20 μA	4.5	3.15	3.15	3.15	·
			6.0	4.2	4.2	4.2	
			2.0	0.5	0.5	0.5	
VII	V <sub>IL</sub> Maximum Low-Level Input Voltage	Vout = 0.1 V or VCC - 0.1 V	3.0	0.9	0.9	0.9	l v l
VIL.		lout  ≤ 20 μA	4.5	1.35	1.35	1.35	_ v
			6.0	1.8	1.8	1.8	
		\/: =\/!!! or\/!!	2.0	1.9	1.9	1.9	
		Vin = VIH or VIL	4.5	4.4	4.4	4.4	.
	Minimum High-Level	l <sub>out</sub>   ≤ 20 μA	6.0	5.9	5.9	5.9	
Voн	OutputVoltage	Vin = VIH or VIL  lout  ≤ 2.4 mA	3.0	2.48	2.34	2.20	V
		I <sub>out</sub>   ≤ 4.0 mA	4.5	3.98	3.84	3.7	
		lout  ≤ 5.2 mA	6.0	5.48	5.34	5.2	
		Vin = VIH or VIL	2.0	0.1	0.1	0.1	
		Vin - ViH OI VIL  lout  ≤ 20 μA	4.5	0.1	0.1	0.1	
	Maximum Low-Level		6.0	0.1	0.1	0.1	
VOL	OutputVoltage	Vin = VIH or VIL  Iout  ≤ 2.4 mA	3.0	0.26	0.33	0.4	V
		lout  ≤ 4.0 mA	4.5	0.26	0.33	0.4	
		lout  ≤ 5.2 mA	6.0	0.26	0.33	0.4	
lin	Maximum Input Leakage Current	Vin = VCC or GND	6.0	0.1	1.0	1.0	μA
Icc	Maximum Quiescent SupplyCurrent (per Package)	Vin = VCC or GND  lout  = 0 μA	6.0	2.0	20	40	μΑ

# AC ELECTRICAL CHARACTERISTICS (CL = 50 pF, Input tr = tf = 6.0 ns)

		Vcc	Gua	Limit		
Symbol	Parameter	(V)	-40 to 25°C	≤85°C	≤125°C	Unit
		2.0	75	95	110	
tPLH,	Maximum Propagation Delay, Input A or B to Output Y	3.0	30	40	55	no
tPHL	(Figures 1 and 2)	4.5	15	19	22	ns
		6.0	13	16	19	
		2.0	75	95	110	
tTLH,	Maximum Output Transition Time, Any Output	3.0	30	40	55	no
tTHL	(Figures 1 and 2)	4.5	15	19	22	ns
		6.0	13	16	19	
Cin	Maximum Input Capacitance		10	10	10	pF

CPD	Dower Dissipation Conscitance (Per Cata)*	Typical @ 25 C, VCC = 5.0 V	
OPD	Power Dissipation Capacitance (Per Gate)*	22 pl	



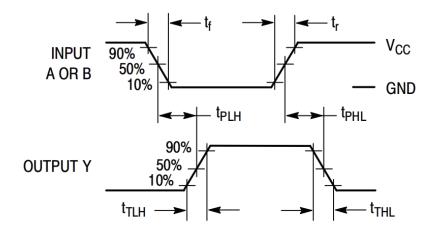
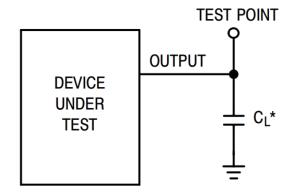


Figure 1. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 2. Test Circuit

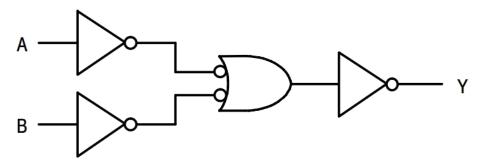
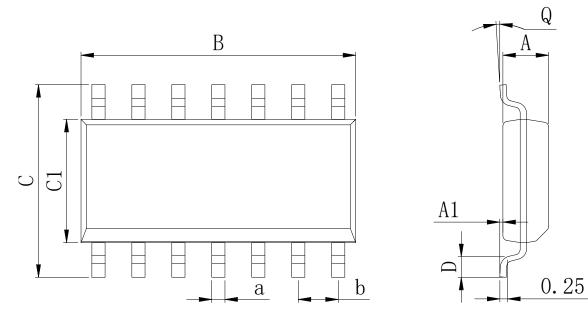


Figure 3. Expanded Logic Diagram (1/4 of the Device)



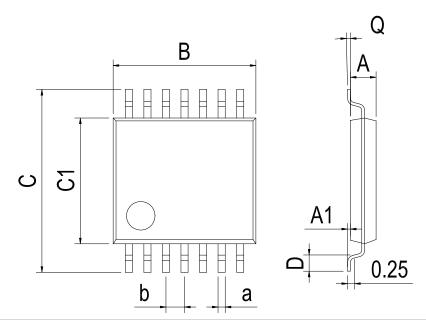
## **PHYSICAL DIMENSIONS**

## SOP-14



Dimensions In Millimeters(SOP-14)									
Symbol:	Α	A1	В	С	C1	D	Q	а	b
Min:	1.35	0.05	8.55	5.80	3.80	0.40	0°	0.35	1.27 BSC
Max:	1.55	0.20	8.75	6.20	4.00	0.80	8°	0.45	1.27 630

TSSOP-14

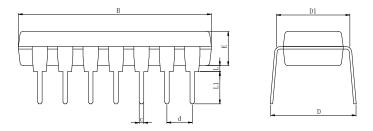


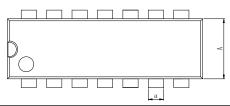
Dimensions In Millimeters(TSSOP-14)									
Symbol:	Α	A1	В	С	C1	D	Q	а	b
Min:	0.85	0.05	4.90	6.20	4.30	0.40	0°	0.20	0.65 BSC
Max:	0.95	0.20	5.10	6.60	4.50	0.80	8°	0.25	0.00 650



# **PHYSICAL DIMENSIONS**

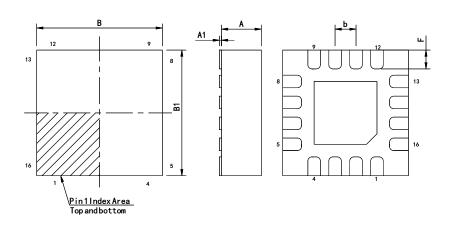
## DIP-14





Dimensions In Millimeters(DIP-14)										
Symbol:	Α	В	D	D1	E	L	L1	а	С	d
Min:	6.10	18.94	8.10	7.42	3.10	0.50	3.00	1.50	0.40	2.54 BSC
Max:	6.68	19.56	10.9	7.82	3.55	0.70	3.60	1.55	0.50	2.54 650

## QFN-16 3\*3



Dimensions In Millimeters(QFN-16 3*3)										
Symbol:	Symbol: A A1 B B1 E F a b									
Min:	0.85	0	2.90	2.90	0.15	0.25	0.18	0.50TYP		
Max:	0.95	0.05	3.10	3.10	0.25	0.45	0.30	0.5011P		



## **REVISION HISTORY**

DATE	REVISION	PAGE
2019-5-9	New	1-9
2023-8-31	Update encapsulation type、Updated DIP-14 dimension	1、7
2024-11-8	Add the QFN-16 package device、Update Lead Temperature	1、3



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